

11. (amended) Projection lens according to claim 8, wherein the first optical element and a second optical element of the sixth optical group enclose a gas chamber, wherein it holds for the radius of curvature R3 of the surface of the second optical element, which faces the first lens, that:

$|R3| > 3000 \text{ mm.}$

12. (amended) Projection lens according to claim 11, wherein it holds for the radius of curvature R3 that: $|R3| > 5000 \text{ mm.}$

13. (amended) Projection lens according to claim 11, wherein it holds for the radius of curvature R4 of the further surface of the second optical element that:

$|R4| > 3000 \text{ mm, preferably } |R4| > 5000 \text{ mm.}$

15. (amended) Projection lens according to claim 8, wherein a lens with an aspheric surface is provided in the first lens cluster.

17. (amended) Projection lens according to claim 15, wherein the aspheric surface is arranged on the first curved surface of the aspheric lens.

25. (amended) System for projection lens according to claim 19, wherein in addition to the manipulation chamber a further at least approximately plane-parallel manipulable gas interspace is provided, for the purpose of removing field curvature, on a substrate, which is to be exposed, in the sixth optical group.

26. (amended) System for projection lens according to claim 20, wherein in addition to the manipulation chamber a further at least approximately plane-parallel manipulable gas interspace is provided, for the purpose of removing field curvature, on a substrate, which is to be exposed, in a sixth optical group.

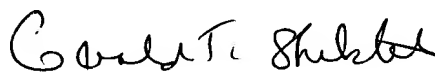
27. (amended) System for projection lens according to claim 21, wherein in addition to the manipulation chamber a further at least approximately plane-parallel manipulable gas interspace is provided, for the purpose of removing field curvature, on a substrate, which is to be exposed, in a sixth optical group.

34. (amended) Method according to claim 29, wherein when the projection lens is being tuned a filling gas is introduced which is subsequently exchanged by the operator for a gas mixture.

36. (amended) Method for producing microstructured components, in the case of which a substrate provided with a light-sensitive layer is exposed by ultraviolet light by means of a mask and a projection exposure machine according to claim 26 and is structured after the development of the light-sensitive layer in accordance with a pattern included on the mask.

Respectfully submitted,

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Dated: May 2, 2001

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